

# PCN#20230728000.2

# Qualification of additional Fab site (DL-LIN) using qualified Process Technology and additional Assembly/Test sites options for select devices Change Notification / Sample Request

Date: July 31, 2023 To: TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) <u>process</u>.

TI requires acknowledgement of receipt of this notification within 30 days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If samples or additional data are required, requests must be received within 30 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 30 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

This particular PCN is related to TI's multiyear transition plan for our two remaining factories with 150-millimeter production (DFAB in Dallas, Texas, and SFAB in Sherman, Texas). DFAB will remain open, but will focus on 200-mm production, with a smaller set of technologies. SFAB will close no earlier than 2024 and no later than 2025. As referenced in the "reason for change" below, these changes are part of our multiyear plan to transition these products to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the Change Management team. For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

Change Management Team SC Business Services

# **Products Affected:**

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TPS76801QPWPRG4Q1	null
TPS76801QPWPRQ1	null
SN65HVD234QDRQ1	null
TLV2372QDRG4Q1	null
TRS3223QPWRQ1	null
TLC082QDGNRQ1	null
TPS76750QPWPRQ1	null
SN65C3221IPWRQ1	null
SN65HVD232QDRQ1	null
SN65HVD251QDRQ1	null

Technical details of this Product Change follow on the next page(s).

PCN Num	ber:	2	0230	72800	0.2			PC	N Date	: Ju	uly 31, 2023
Title:	-				ab site (DL-L sites options fo	, .	•		Process	s Tech	nnology and
Customer Contact:         Change Management team         Dept:         Quality Services						ity Services					
Proposed 1 <sup>st</sup> Ship Date: Jan 31, 2024							uests until:	Aug	31, 2023*		
*Sample	requests	s receiv	ed af	fter A	ug 31, 2023 <mark>w</mark>	ill not be	e sup	port	ted.		
Change Ty											
🛛 Assemt					esign						p Material
🛛 Assemb			[		ata Sheet				Wafer	Bum	p Process
🛛 Assemt	oly Mater	ials	[		art number ch	ange		$\boxtimes$	Wafer	Fab S	Site
	nical Spec			_	est Site			$\square$			Materials
Packing	g/Shippin	g/Labeli	ng	Τε	est Process				Wafer	· Fab I	Process
					PCN De	tails					
Qualificatio	on of add	itional Fa		-	·LIN) using qu	alified Pr					
Qualificatio	on of add	itional Fa		-		alified Pr					
-	on of add Test site:	itional Fa	s for t	the list	LIN) using qu of devices in	alified Pr	uct af	fect	ed secti	ion be	
Qualificatio	on of add Test sites Cu It Fab	itional Fa s options	for t Fab	Site	LIN) using qu of devices in	alified Pr the prod	uct af Ad	fect dit	ed secti	ion be	site Wafer

	Current	Additional
Probe Site	DFAB	CDPR

# Group 2 (DFAB8 qualification plus Cu) BOM Table

	Current	Additional
Bond wire composition, diameter	Au, 0.96 mil	Cu, 1.0 mil

# Group 3 (DFAB8 qualification plus BOM changes) BOM Table

	Current	Additional
Mold Compound	4206193	4211471
Bond wire composition, diameter	Au, 0.96 mil	Cu, 1.0 mil
Mount Compound	4042500	4147858

# Group 4 (DFAB8 qualification plus PHI as additional site) BOM Table

	LEN	PHI
Mold Compound	SID#0011G60007	4222198
Bond wire composition, diameter	Au, 1.0 mil	Cu, 1.0 mil
Mount Compound	SID#0003C10332	8095733

Lead finish	NiPdAu	Matte Sn
Final Test site	LEN	PHI

# Group 5 (DFAB8 qualification plus CDAT as additional Assembly site)BOM Table

	LEN	CDAT
Mold Compound	SID#0011G60007	4222198
Bond wire composition,	Au, 1.0 mil	Cu, 1.0 mil
diameter		
Mount Compound	SID#0003C10332	4207123
Lead finish	NiPdAu	Matte Sn
Probe Site	DFAB	CDPR
Final Test Site	LEN	CDAT

Upon expiry of this PCN, there will be a transition period where TI will combine lead free solutions in a single <u>standard part number</u>. For example; <u>TLV2381IDBVT</u> – can ship with both Matte Sn and NiPdAu.

Example:

- Customer order for 7500 units of TLV2381IDBVT with 2500 units SPQ (Standard Pack Quantity per Reel).
- TI can satisfy the above order in one of the following ways.
  - I. 3 Reels of NiPdAu finish.
  - II. 3 Reels of Matte Sn finish
  - III. 2 Reels of Matte Sn and 1 reel of NiPdAu finish.
  - IV. 2 Reels of NiPdAu and 1 reel of Matte Sn finish.

Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ

Qual details are provided in the Qual Data Section.

# **Reason for Change:**

These changes are part of our multiyear plan to transition products from our 150-milimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

# Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
🛛 No Change	🛛 No Change	🛛 No Change	🛛 No Change

Changes to product identification resulting from this PCN:

# Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
DL-LIN	DLN	USA	Dallas

# **Assembly Site Information:**

Assembly Site Assembly Site Origin (22L	Assembly Country Code (23L)	Assembly City
---	--------------------------------	---------------

LEN	LIN	TWN	Taichung
CDAT	CDA	CHN	Chengdu
TIPI	PHI	PHL	Baguio City

Sample product shipping label (not actual product label)



Toup I Device list (D	FAB8 qualification only	)	
MLA00300DR	TLV2402QDGKRQ1	TPS3307-18QDRG4Q1	TPS76833QPWPRQ1
MLA00346PWPR	TLV2472QDRG4Q1	TPS3307-18QDRQ1	TPS76850QPWPRQ1
SN65HVD230QDR	TLV2472QDRQ1	TPS76733QPWPRQ1	TPS77501QPWPRQ1
SN65HVD231QD	TPS3306-15QDRG4Q1	TPS76750QPWPRQ1	TPS77533QPWPRCT
SN65HVD231QDG4	TPS3306-15QDRQ1	TPS76801QPWPRG4CT	TPS77533QPWPRQ1
SN65HVD231QDR	TPS3306-18QDRG4Q1	TPS76801QPWPRG4Q1	TPS77601QPWPRG4C
SN65HVD232QD	TPS3306-18QDRQ1	TPS76801QPWPRMO	TPS77601QPWPRG4Q
SN65HVD232QDG4	TPS3306-25QDRG4Q1	TPS76801QPWPRQ1	TPS77601QPWPRQ1
	TPS3306-33QDRG4Q1	TPS76818QPWPRQ1	TPS77633QPWPRQ1
SN65HVD232QDR	11-22200-22000404		τ τ τ
	TPS3306-33QDRQ1	TPS76825QPWPRQ1	TPS77733QDRVS
SN65HVD233QDRQ1 SN65HVD234QDRQ1	TPS3306-33QDRQ1	TPS76825QPWPRQ1	
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Group 1A Device list (1 TLC082QDGNRQ1		TPS76825QPWPRQ1	
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Froup 1A Device list ( TLC082QDGNRQ1 Froup 2 Device list (D	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1	TPS76825QPWPRQ1	TPS77733QDRVS
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Froup 1A Device list (1 TLC082QDGNRQ1 Froup 2 Device list (DI SN65HVD230QDG4Q1	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus	TPS76825QPWPRQ1 s Probe site) TLV272QDRG4Q1 Cu)	TPS77733QDRVS
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Froup 1A Device list ( TLC082QDGNRQ1 Froup 2 Device list (DI SN65HVD230QDG4Q1 SN65HVD230QDRG4Q1	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus SN65HVD232QDRG4Q1	TPS76825QPWPRQ1 IS Probe site) TLV272QDRG4Q1 Cu) TLV2472AQDRG4Q1	TPS77733QDRVS
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Group 1A Device list (1 TLC082QDGNRQ1 Group 2 Device list (DI SN65HVD230QDG4Q1 SN65HVD230QDRG4Q1 SN65HVD231QDRG4Q1	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus SN65HVD232QDRG4Q1 SN65HVD232QDRQ1	TPS76825QPWPRQ1 S Probe site) TLV272QDRG4Q1 Cu) TLV2472AQDRG4Q1 MLA00127PWPR	TPS77733QDRVS TPS767D301QPWPRQ TPS767D318QPWPRQ
TLC082QDGNRQ1	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus SN65HVD232QDRG4Q1 SN65HVD232QDRQ1 SN65HVD251QDRMO	TPS76825QPWPRQ1         IS Probe site)         TLV272QDRG4Q1         Cu)         TLV2472AQDRG4Q1         MLA00127PWPR         MLA00128PWPR	TPS77733QDRVS TPS767D301QPWPRQ TPS767D318QPWPRQ SN65C3221IPWRQ1
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Group 1A Device list (1 TLC082QDGNRQ1 SN65HVD230QDG4Q1 SN65HVD230QDRG4Q1 SN65HVD231QDRG4Q1 SN65HVD231QDRQ1 SN65HVD232QDRG4	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus SN65HVD232QDRG4Q1 SN65HVD232QDRQ1 SN65HVD251QDRMO SN65HVD251QDRQ1	TPS76825QPWPRQ1         IS Probe site)         TLV272QDRG4Q1         Cu)         TLV2472AQDRG4Q1         MLA00127PWPR         MLA00128PWPR         MLA00340PWPR         MLA00341PWPR	TPS77733QDRVS TPS767D301QPWPRQ TPS767D318QPWPRQ SN65C3221IPWRQ1
SN65HVD233QDRQ1 SN65HVD234QDRQ1 Group 1A Device list (1 TLC082QDGNRQ1 SN65HVD230QDG4Q1 SN65HVD230QDRG4Q1 SN65HVD231QDRG4Q1 SN65HVD231QDRQ1 SN65HVD232QDRG4	TPS3306-33QDRQ1 DFAB8 qualification plu TLV2372QDRG4Q1 FAB8 qualification plus SN65HVD232QDRG4Q1 SN65HVD232QDRQ1 SN65HVD251QDRMO SN65HVD251QDRQ1 SN65HVD251QDRSV	TPS76825QPWPRQ1         IS Probe site)         TLV272QDRG4Q1         Cu)         TLV2472AQDRG4Q1         MLA00127PWPR         MLA00128PWPR         MLA00340PWPR         MLA00341PWPR	TPS77733QDRVS TPS767D301QPWPRQ TPS767D318QPWPRQ SN65C3221IPWRQ1

# Group 5 Device list (DFAB8 qualification plus CDAT as additional Assembly site)

TPS3836J25QDBVRQ1 TPS3836K33QDBVRQ1 TPS3836L30QDBVRQ1

For alternate parts with similar or improved performance, please visit the product page on  $\underline{\text{TI.com}}$ 



#### Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

## Approved 25-Aug-2016

### Product Attributes

Attributes	Qual Device: ALM2402QPWPRQ1	QBS Process Reference: TPS51604QDSGQ1			
Operating Temp Range	-40 to +125 C	-40 to +125 C			
Automotive Grade Level	Grade 1	Grade 1			
Product Function	Signal Chain	Power Management			
Wafer Fab Supplier	RFAB	RFAB			
Die Revision	A0	A			
Assembly Site	TAI	CLARK-AT			
Package Type	HTSSOP	WSON			
Package Designator	PWP	DSG			
Ball/Lead Count	14	8			

- QBS: Qual By Similarity - Qual Device ALM2402QPWPRQ1 is qualified at LEVEL3-260C

#### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Qty Lot		Qual Device: ALM2402QPWPRQ1	QBS Process Reference: TPS51604QDSGQ1				
		Test Group A – Acc	elerated I		ment Stress Tests			
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning	Level 3-260C	3/1000/1 (Note 1)	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	60	Post Temp Cycle Bond Pull	per MIL-STD 883 Method 2011	1/30/0	1/30/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, - 40/125C 1000 Cycles		1/45/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	-	3/135/0
HTSL	High Tomp Storage Bake		500 hours	1/45/0	-			
		Test Group B – Acc	elerated l	Lifetime	e Simulation Tests			
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	-	3/231/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	300 Hours	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/0
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-
		Test Group C – P	ackage A	ssembl				
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	3/90/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb-Free	3/45/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	3/45/0	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	3/30/0	3/30/0
		Test Group D –	Die Fabric	ation R	eliability Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		Test Group E	<ul> <li>Electric</li> </ul>	al Verif	ication Tests			
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	250 V	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/12/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67	3/90/0	3/90/0

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or C): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note (1): One continuity failure due to mishandling - discounted.

TI Qualification ID: 20150211-111605



### **Automotive New Product Qualification Summary**

(As per AEC-Q100 and JEDEC Guidelines)

#### Q100 Grade-1 qual for ALM2402QPWPRQ1 (RFAB/LBC7/D-Cu) in TAI using 14-pin TSSOP pkg (PWP) , per AEC Q100 Rev H Approved 25-Aug-2016

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: ALM2402QPWPRQ1	QBS Process Reference TPS51604QDSGQ1
		Test Group A – Acc		Enviror	ment Stress Tests			
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning	Level 3-260C	3/1000/1 (Note 1)	
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	60	Post Temp Cycle Bond Pull	Method 2011		1/30/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, - 40/125C	1000 Cycles	1/45/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 175C	500 hours	1/45/0	-
		Test Group B – Acc	elerated	Lifetim	e Simulation Tests			
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	-	3/231/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	300 Hours	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/0
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-
		Test Group C – P	ackage A	ssembl	y Integrity Tests			
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	3/90/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb-Free	3/45/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	3/45/0	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)		3/30/0	3/30/0
		Test Group D – I	Die Fabri	cation <b>B</b>	eliahility Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		Test Group E		_				
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	250 V	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/12/0
ED	E6	AEC 0100 000	3	20	Electrical Distributions	Cpk>1.67	2/00/0	3/00/0

**Qualification Results** Data Displayed as: Number of lots / Total sample size / Total failed

ED

- OBS: Qual by Similarity - Qual Device ALM24020PWPRQ1 is qualified at LEVEL3-260C A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

AEC Q100-009

30

Electrical Distributions

Cpk>1.67

3/90/0

3/90/0

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E5

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot TMB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note (1): One continuity failure due to mishandling - discounted.

TI Qualification ID: 20150211-111605



### Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines) Approve Date 11-Feb-2020

#### Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>	QBS Process Reference: <u>MAX3243IPWG4DL</u>
			roup A – A	ccelerate	d Environment Stress Tests			
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning Level 1	Level 1-260C	3/1199/0	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 150C	1000 Hours	-	3/231/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	3/135/0	-
		Test G	roup B – A	ccelerate	d Lifetime Simulation Tests			
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	3/231/0	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C			3/2400/0
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-
		Test	Group C –	Package	Assembly Integrity Tests			
WBP	C1	AEC Q100-001	1	30	Bond Pull, over ball	Minimum of 5 devices, 30 wires Cpk>1.67	3/90/0	1/30/0
WBP	C1	AEC Q100-001	1	30	Bond Pull, over stitch 30 wires Cpk +1.67		3/90/0	1/30/0
WBS	C1	AEC Q100-001	1	30	Auto Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	3/90/0	-
Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>	QBS Process Reference: <u>MAX3243IPWG4DL</u>
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	1/15/0	-
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	3/30/0
LI	C6	JEDEC JESD22-B105	1	22	Lead Pull to Destruction	Leads	1/22/0	-
		Test	Group D -	- Die Fabr	ication Reliability Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35		-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-		-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-		-	Stress Migration	-	Completed Per Process Technology Requirements	-
		Te	est Group	E – Ele <u>ctr</u>	ical Verification Tests			
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	500 V (1)	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-

AEC Q100-004

AEC Q100-009

1

3

6

30

Latch-up

Auto Electrical Distributions

LU E4

ED E5

Per AEC-Q100-004

Cpk>1.67

-

-

1/6/0

3/90/0

- QBS: Qual by Similarity - Qual Device TLV2401QDBVRQ1 is qualified at LEVEL1-260C A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

 Ambient Operating Temperature by Automotive Grade Level:
 Grade 0 (or E): -40°C to +150°C
 Grade 1 (or Q): -40°C to +125°C
 Grade 2 (or T): -40°C to +105°C
 Grade 3 (or I): -40°C to +85°C
 Grade 3 (or I): -40°C to +

### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green Note (1): See ESD waiver attached to eQDB. Change Number: NA TI Qualification ID: 20190124-128331



**TI Information** Selective Disclosure

Automotive New Product Qualification Summary

### Approved 07-Sep-2016

#### Product Attributes

Attributes	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C	
Product Function	Interface	Interface	Interface	
Wafer Fab Supplier	DFAB	DFAB	DFAB	
Die Revision	A	A	A	
Assembly Site	FMX	FMX	FMX	
Package Type	SOIC	SOIC	SOIC	
Package Designator	D	D	D	
Ball/Lead Count	8	8	8	

 Ball/Lead Count
 8
 8

 - QBS: Qual By Similarity
 - Qual Device SN65HVD233QDRQ1, Qual Device SN65HVD234QDRQ1 is qualified at LEVEL1-260C

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1
		Test Group A –	Accelerate	d Envir					
-	-	-	-	-	SAM Analysis Post Precon	Completed	1/22/0	1/22/0	1/22/0
PC	A1	JEDEC J-STD-020 JESD22-A113	-	-	Preconditioning	Level 1- 260C	No Fails	No Fails	No Fails
-	-	-	-	-	SAM Analysis Post Precon	Completed	1/22/0	1/22/0	1/22/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST 130C/85%RH	96 Hours	1/77/0	1/77/0	1/77/0
-	-	-	3	1	Cross Section Post bHAST 96 Hours	Completed	1/1/0	1/1/0	1/1/0
-	-	-	3	22	SAM Analysis Post bHAST 96 Hours	Completed	1/22/0	1/22/0	1/22/0
-	-	-	3	30	Wire Bond Shear Post bHAST 96 Hours	Wires	1/30/0	1/30/0	

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1
-	-	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	1/30/0	1/30/0	-
-	-	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	1/30/0	1/30/0	-
HAST	A2	JEDEC JESD22-A110	3	70	Biased HAST 130C/85%RH	192 Hours	1/70/0	1/70/0	1/70/0
-	-	-	3	1	Cross Section Post bHAST 192 Hours	Completed	1/1/0	1/1/0	1/1/0
-	-	-	3	22	SAM Analysis Post bHAST 192 Hours	Completed	1/22/0	1/22/0	1/22/0
-	-	-	3	30	Wire Bond Shear Post bHAST 192 Hours	Wires	1/20/0 (1)	1/30/0	1/30/0
-	-	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	1/30/0	1/30/0	1/30/0
-	-	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	1/20/0 (1)	1/30/0	1/30/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle -65/150C	500 Cycles	1/77/0	1/77/0	1/77/0
-	-	-	3	1	Cross Section Post T/C 500 Cycles	Completed	1/1/0	1/1/0	1/1/0
-	-	-	3	22	SAM Analysis Post T/C 500 Cycles	Completed	1/22/0	1/22/0	1/22/0
TC- WBS	-	-	3	30	Wire Bond Shear Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle -65/150C	1000 Cycles	1/70/0	1/70/0	1/70/0
	-	-	3	1	Cross Section Post T/C 1000 Cycles	Completed	1/1/0	1/1/0	1/1/0
	-	-	3	22	SAM Analysis Post T/C 1000 Cycles	Completed	1/22/0	1/22/0	1/22/0
TC- WBS	-	-	3	30	Wire Bond Shear Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Ball Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Stitch Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
РТС	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	1000 Cycles	N/A	N/A	N/A
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	2000 Cycles	N/A	N/A	N/A

	Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1
	HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	1/45/0	1/45/0	1/45/0
	-	-	-	3	1	Cross Section Post Bake 1000 Hours	Completed	1/1/0	1/1/0	1/1/0
	HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	1/44/0	1/44/0	1/44/0
	-	-	-	3	1	Cross Section Post Bake 2000 Hours	Completed	1/1/0	1/1/0	1/1/0
T	est Group	0 C – F	Package Assembly Integri	ity Tests						
	WBS	C1	AEC Q100-001	3	30	Wire Bond Shear Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0
	WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I)...: -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20160217-116814

Notes/ Comments: (1) Performed on only 2 devices



### Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

TPS3840PH30DBVRQ1 (Q100, Grade 1, -40 to 125C)

### Approved 02-Jun-2022

#### **Product Attributes**

Attributes	Qual Device: <u>TM\$3840PH30DBVRQ1</u>
Automotive Grade Level	Grade 1
Operating Temp Range	-40 to +125 C
Product Function	Power Management
Wafer Fab Supplier	RFAB
Die Revision	A
Assembly Site	CDAT
Package Type	SOT-23
Package Designator	DBV
Ball/Lead Count	5

- QBS: Qual By Similarity - Qual Device 3840PH30DBVRQ1 is qualified at LEVEL1-260CG

#### Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>3840PH30DBVRQ1</u>
		Test Gro	oup A – Accelei	rated Envi	ronment Stress Tests		
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1-260C	No Fails
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0
UHAST	A3	JEDEC JESD22-A102	3	77	Unbiased HAST 130C/85%RH	96 Hours	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
TC-WBF	P A4	MIL-STD883 Method 2011	1	60	Post Temp Cycle Bond Pull	Wires	3/108/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 150C	1000 Hours	3/231/0
		Test Gr	oup B – Accele	rated Lifet	ime Simulation Tests		
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	3/231/0
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A
		Test C	Group C – Pack	age Asser	nbly Integrity Tests		
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear, Cpk>1.67	Wires	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull, Cpk>1.67	Wires	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free Solder	3/45/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Solder	3/45/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	<u>Cpk</u> >1.67	3/30/0
LI	C6	JEDEC JESD22-B105	1	50	Lead Fatigue	Leads	3/66/0
LI	C6	JEDEC JESD22-B105	1	50	Lead Pull to Destruction	Leads	3/66/0

			Т	est G	roup D – Die Fabrication Reliability Tests				
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements		
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements		
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements		
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements		
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements		
Test Group E – Electrical Verification Tests									
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0		

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +155°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +125°C Grade 3 (or I): -40°C to +85°C

# E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

#### Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20201126-137339



**TI Information** Selective Disclosure

# Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

# SN3257QPWRQ1 (Grade 1, Q100H, -40/125C) Approved 13-Feb-2020

# **Product Attributes**

Attributes	Qual Device: <u>SN3257QPWRQ1</u>	QBS Process Reference: <u>SN3257QDYYRQ1</u>		
Automotive Grade Level	Grade 1	Grade 1		
Operating Temp Range	-40 to +125 C	-40 to +125 C Interface RFAB		
Product Function	Interface			
Wafer Fab Supplier	RFAB			
Die Revision	A	Α		
Assembly Site	MLA	PHI		
Package Type	TSSOP	SOT-23		
Package Designator	PW	DYY		
Ball/Lead Count	16	16		

- QBS: Qual By Similarity

- Qual Device SN3257QPWRQ1 is qualified at LEVEL1-260C

Data Displayed as: Number of lots / Total sample size / Total failed										
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: <u>SN3257QPWRQ1</u>	QBS Process Reference: <u>SN3257QDYYRQ</u> 1		
		Test Group A – A	ccelerat	ed Envi	ronment Stress Tests					
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	Level 1- 260C No Fails		-		
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-		
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	3/231/0	-		
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, - 55/150C	1000 Cycles	3/231/0	-		
TC- WBP	A4	MIL-STD883 Method 2011	1	60	Bond Pull Post Temp Cycle	Wires	1/60/0	-		
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-		
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	3/135/0	-		
		Test Group B – A	ccelerat	ed Life	time Simulation Tests					
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	300 Hours	3/231/0	3/231/0		
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0		
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-		
		Test Group C -	Packag	e Assei	mbly Integrity Tests					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear, Cpk >1.67	Wires	3/90/0	-		
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull, Cpk >1.67	Wires	3/90/0	-		
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	PB Solder	1/15/0	-		
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free Solder	1/15/0	-		
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	3/30/0	-		
		Test Group D	– Die Fa	bricatio	on Reliability Tests					
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-		
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-		
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-		
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-		
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology	-		

#### Qualification Results er of lots / Total sample size / Total failed Data Displayed as: Nur

Test Group E – Electrical Verification Tests									
	HBM	E2	AEC Q100-002	1	3	ESD - HBM	5000 V	1/3/0	-
	CDM	E3	AEC Q100-011	1	3	ESD - CDM	2000 V	1/3/0	-
	LU	E4	AEC Q100-004	1	6	Latch-up	Per AEC Q100-004	1/6/0	-
	ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk >1.67	3/90/0	-

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

 $\label{eq:amplitude} \begin{array}{l} \mbox{Ambient Operating Temperature by Automotive Grade Level:} \\ \mbox{Grade 0 (or E): } -40^\circ C \ to +150^\circ C \\ \mbox{Grade 1 (or Q): } -40^\circ C \ to +125^\circ C \\ \mbox{Grade 2 (or T): } -40^\circ C \ to +105^\circ C \\ \mbox{Grade 3 (or I): } -40^\circ C \ to +85^\circ C \\ \end{array}$ 

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

# Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20190311-128972



### Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### Approved 11-Feb-2020

#### Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>				
Test Group A – Accelerated Environment Stress Tests											
PC	A1	-	3	22	SAM Analysis, Pre-Stress	Completed	2/44/0				
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1-260C	No fails				
PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	3/66/0				
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0				
HAST	A2	-	3	1	Cross Section, Post bHAST 96 Hours	Completed	3/3/0				
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 96 Hours	Wires	3/90/0				
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	3/90/0				
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	3/90/0				
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	192 Hours	3/210/0				
HAST	A2	-	3	1	Cross Section, Post bHAST 192 Hours	Completed	3/3/0				
HAST	A2	-	3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	3/66/0				
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 192 Hours	Wires	3/60/0				
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	3/60/0				
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	3/60/0				
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0				

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>	
	TC	A4	-	3	1	Cross Section, Post T/C 500 Cycles	Completed	3/3/0	
	TC	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	3/66/0	
	тс	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	3/90/0	
	тс	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	3/90/0	
	тс	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	3/90/0	
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	1000 Cycles	3/210/0	
	тс	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0	
	тс	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	3/66/0	
	тс	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/60/0	
	тс	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/60/0	
	тс	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/60/0	
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	1000 Cycles	N/A	
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	2000 Cycles	N/A	
H	HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	3/135/0	
H	HTSL	A6	-	3	1	Cross Section, Post HTSL 1000 Hours	Completed	3/3/0	
H	HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	3/132/0	
H	HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	3/3/0	
Test Group C – Package Assembly Integrity Tests									
	WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cpk>1.67	Wires	3/30/0	
'	WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cpk >1.67	Wires	3/30/0	

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

 Ambient Operating Temperature by Automotive Grade Level:
 Grade 0 (or E): -40C to +150C
 Grade 1 (or Q): -40C to +125C
 Grade 2 (or T): -40C to +105C
 Grade 3 (or I): -40C to +85C
 Grad 3 (or I): -40C to +85C
 Grad 3 (or I):

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20190124-128331

# ZVEI ID: SEM-PW-02, SEM-PW-13, SEM-TF-01, SEM-PA-08, SEM-PA-11, SEM-PA-07, SEM-PA-18, SEM-PA-05

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disdaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (<u>www.ti.com/legal/termsofsale.html</u>) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.